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In re application of:

Art Unit: Not assigned

Ken NAKAHARA

Examiner: Not assigned

Serial No: Not assigned

Filed: February 4, 2004

ZnO SYSTEM SEMICONDUCTOR DEVICE

TRANSMITTAL OF INFORMATION DISCLOSURE **STATEMENT**

Mail Stop PATENT APPLICATION Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

The information disclosure statement submitted herewith is being filed concurrently with the subject application [37 C.F.R. § 1.97(b)] and contains no items of information cited in any communication from a foreign patent office in a counterpart foreign application [37 C.F.R. § 1.97(e)(1)].

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

If it should be determined that for any reason either an insufficient or excessive fee has been paid, please charge any insufficiency or credit any overpayment necessary to ensure consideration of the information disclosure statement for the above-identified application to Deposit Account No. 50-1314. A copy of this paper is enclosed.

Respectfully submitted,

HOGAN & HARTSON L.L.P.

Date: February 4, 2004

Dariush G. Adli

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Facsimile: 213-337-6701

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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INFORMATION DISCLOSURE CITATION IN AN APPLICATION			Applicant Ken NAKAHARA			
(Use several sheets if necessary)			Filing Date February 4, 2004		Group Art Unit Not assigned	
U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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FOREIGN PATENT DOCUMENTS						
4.	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION (YES/NO)
=	2002-118330	04/19/02	Japan			Abstract
.:						
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
	Soon-Ku Hong et al., "Control of polarity of ZnO films grown by plasma-assisted molecular-beam epitaxy: Zn- and O-polar ZnO films on Ga-polar GaN templates", Applied Physics Letters, Vol. 77, No. 22, November 27, 2000, pp. 3571-3573					
	D.C. Look et al., "Characterization of homoepitaxial <i>p</i> -type ZnO grown by molecular beam epitaxy", Applied Physics Letters, Vol. 81, No. 10, September 2, 2002, pp. 1830-1832.					
EXAMINER		DATE CONSIDERED				
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.						